

*AMENDMENTS TO THE CLAIMS*

1. (Currently Amended) An integrated circuit device comprising:  
a semiconductor amplification element supplied with a voltage from a first power source; and  
a bias circuit for applying a bias voltage to the semiconductor amplification element, wherein  
the bias circuit is supplied with a second voltage from a second power source,  
and  
the second power source is connected to the first power source via a ~~semiconductor element diode~~, and idle current of the semiconductor amplification element ~~changes~~ change in response to a change of the voltage supplied by the first power source to the semiconductor amplification element.

Claims 2 and 3 (Cancelled).

4. (Previously Presented) The integrated circuit device according to Claim 1, which acts as a power amplifier circuit, including a transistor as the semiconductor amplification element, wherein the bias circuit includes a bias generating circuit for generating a base bias of the transistor and a temperature compensation circuit for temperature compensation of the bias generating circuit.

This listing of claims replaces all prior versions, and listings, of claims in the application.